

Silicon NPN Power Transistors

BU2508D

DESCRIPTION

- With TO-3PN package
- High voltage;high speed
- Built-in damper diode

APPLICATIONS

- For use in horizontal deflection circuits of colour TV receivers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

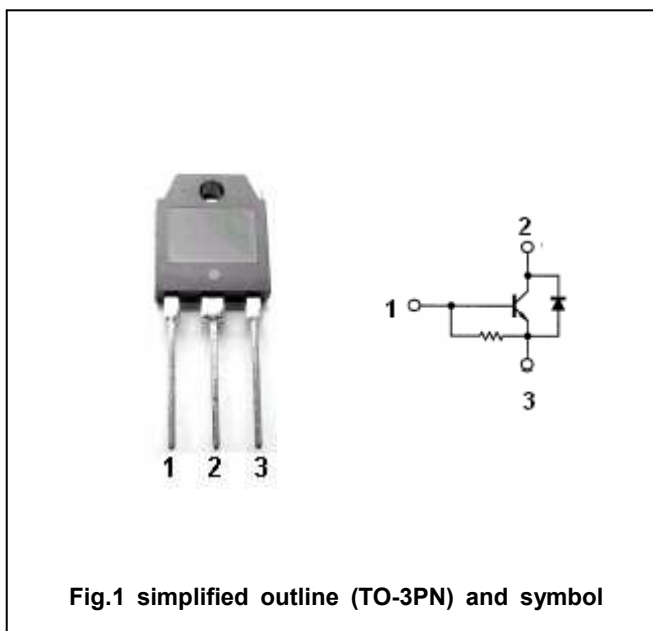


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1200	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	700	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7.5	V
I <sub>C</sub>	Collector current		8	A
I <sub>CM</sub>	Collector current-peak		15	A
I <sub>B</sub>	Base current		4	A
I <sub>BM</sub>	Base current-peak		6	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	125	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A; I <sub>B</sub> =0, L=25mH	700			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =600mA; I <sub>C</sub> =0	7.5	13.5		V
V <sub>CE(sat-1)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A; I <sub>B</sub> =1.1A			5.0	V
V <sub>CE(sat-2)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A; I <sub>B</sub> =1.29A			1.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5A; I <sub>B</sub> =1.7A			1.3	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =rated; V <sub>BE</sub> =0 T=125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7.5V; I <sub>C</sub> =0	140		390	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	7	13	23	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =4.5A; V <sub>CE</sub> =1V	4	5.5	7.5	
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =4.5A		1.6	2.0	V
C <sub>C</sub>	Collector capacitance	V <sub>CB</sub> =10V; f=1MHz		80		pF

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PACKAGE OUTLINE

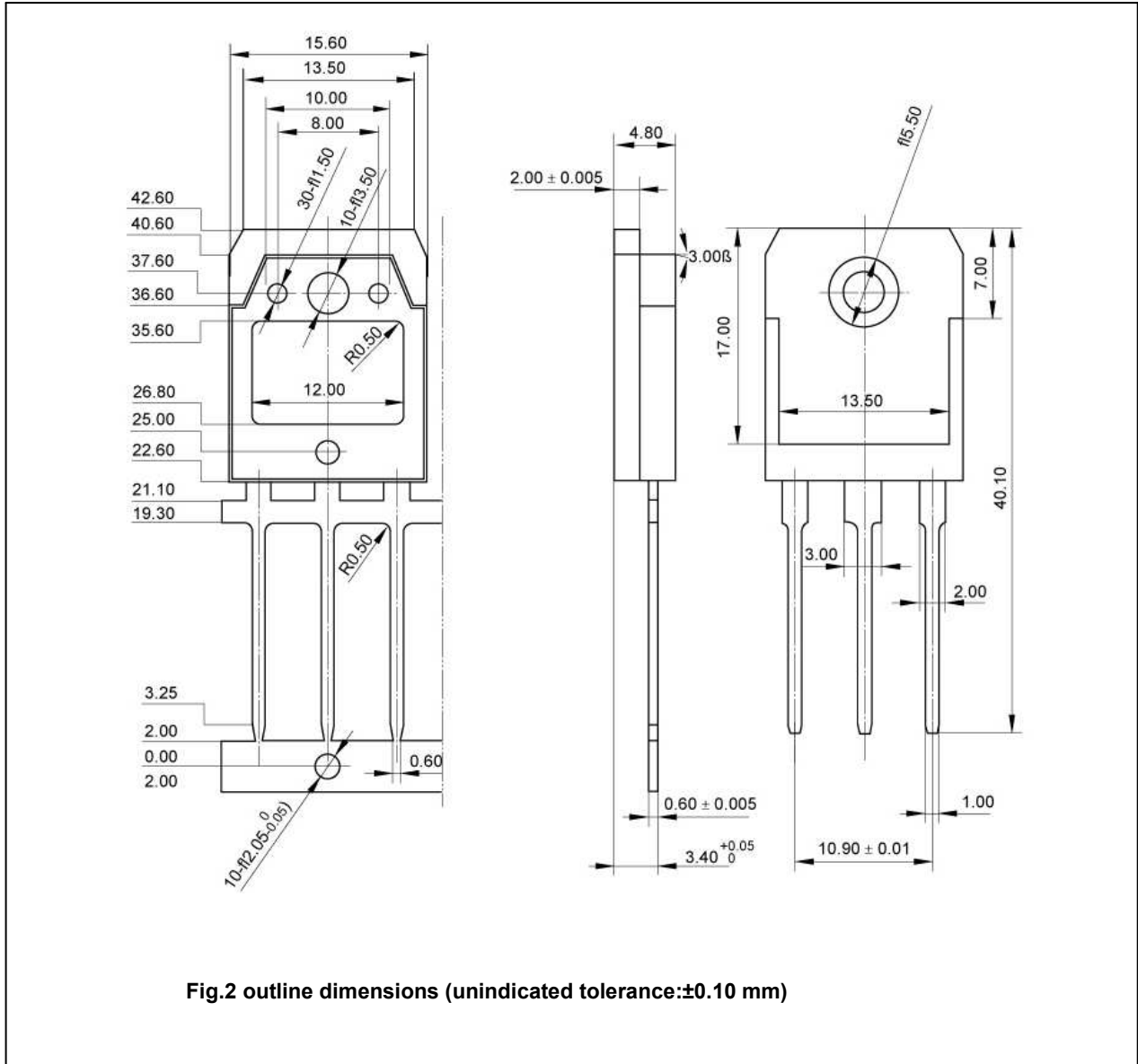


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)